



2SD235

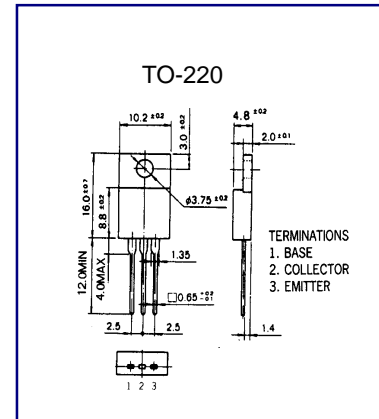
NPN EPITAXIAL SILICON TRANSISTOR

LOW FREQUENCY POWER AMPLIFIER

- Complement to 2SB435

ABSOLUTE MAXIMUM RATINGS ($T_A=25^\circ\text{C}$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	50	V
Collector-Emitter Voltage	V _{CE0}	40	V
Emitter-Base voltage	V _{EB0}	5	V
Collector Current (DC)	I _C	3	A
Collector Dissipation ($T_c=25^\circ\text{C}$)	P _C	25	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-50~150	°C



ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I _{CBO}	V _{CB} = 50V , I _E =0			10	μA
Emitter Cutoff Current	I _{EB0}	V _{EB} = 5V , I _C =0			10	μA
DC Current Gain	h _{FE1}	V _{CE} = 5V , I _C =0.5A	40		240	
Collector- Emitter Saturation Voltage	V _{CE(sat)}	I _C =3A , I _B =0.3A			1.0	V
Current Gain Bandwidth Product	f _T	V _{CE} = 2V , I _C =0.5A		18		MHZ